

Radiation	Type	Technology	Electrodes
Red	Point Source	AlInGaP/GaAs	N (cathode) up

	typ. dimensions (μm)	
	typ. thickness 170 (±20) μm  cathode gold alloy, 1.5 μm  anode gold alloy, 0.5 μm	

## Maximum Ratings

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I <sub>F</sub>			10	mA

## Optical and Electrical Characteristics

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 5 mA	V <sub>F</sub>		2.0	2.5	V
Reverse voltage	I <sub>R</sub> = 10 μA	V <sub>R</sub>	5			V
Radiant power*	I <sub>F</sub> = 5 mA	Φ <sub>e</sub>	40	55		μW
Luminous intensity*	I <sub>F</sub> = 5 mA	I <sub>v</sub>	1.7	2.5		mcd
Peak wavelength	I <sub>F</sub> = 5 mA	λ <sub>p</sub>	635	645	660	nm
Spectral bandwidth at 50%	I <sub>F</sub> = 5 mA	Δλ <sub>0.5</sub>		25		nm
Switching time	I <sub>F</sub> = 5 mA	t <sub>r</sub> , t <sub>f</sub>		40/30		ns

\*Measured on bare chip on TO-18 header with *EPIGAP* equipment

## Labeling

Type	Lot N°	Φ <sub>e</sub> (typ) [mW]	V <sub>F</sub> (typ) [V]	Quantity
ELC-645-29-20				

**Packing:** Chips on adhesive film with wire-bond side on top